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AF/2811

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Kunihiro TAKATANI

Serial No.: 09/557,961

Filing Date: April 25, 2000

For: ELECTRODE STRUCTURE ON P-TYPE
III GROUP NITRIDE SEMICONDUCTOR
LAYER AND FORMATION METHOD
THEREOF

Examiner: Donghee Kang

Group Art Unit: 2811

AMENDMENT UNDER 37 CFR 1.116

Mail Stop - AF

Commissioner for Patents
2011 South Clark Place
Room 1B03, Crystal Plaza 2
Arlington, VA 22202

Sir:

In response to the Final Office Action dated May, 28, 2004, please reconsider this application in view of the following remarks.

REMARKS

Claims 8-10 and 12 stand rejected under 35 USC 103(a) as being unpatentable over Shibata. This rejection is respectfully traversed.

In paragraph 2 of the final office action the Examiner states:

Shibata et al. do not teach the third electrode layer covering an entire area of ohmic contact area. As described on page 8, line 32 to page 9, line 7, Shibata et al. found that the exposed Ni layer can react with N₂ in the atmosphere preventing good ohmic characteristic (see argument of application, on page 6). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to cover the entire Ni layer to prevent the reaction with N₂ because the reaction prevents good ohmic characteristics.